

East - (1064115.wsp.1)

File View Edit Tools Window Help

(21) "5736764"
 (0) 6680227.URPN.
 (7) ("5070378" | "5200733" | "5852317" | "5966603" |
 (13) "NROM" and (antenna adj effect)
 (18) "NROM" and (antenna)
 (5) ("NROM" and (antenna)) not ("NROM" and (antenna a
 (5377) ((non-volatile or (non adj volatile)) adj mem
 (5358) (((non-volatile or (non adj volatile)) adj mem
 (55) kuo-tung-cheng.in. liu-chien-hung.in. pan-shyi-s
 (5347) (((non-volatile or (non adj volatile)) adj me
 (2923) (((non-volatile or (non adj volatile)) adj n
 (3287) (((non-volatile or (non adj volatile)) adj n
 (46) (((non-volatile or (non adj volatile)) adj me
 (17) (((non-volatile or (non adj volatile)) adj n
 (29) (((non-volatile or (non adj volatile)) adj n
 (3241) (((non-volatile or (non adj volatile)) adj
 (1235) (((non-volatile or (non adj volatile)) adj
 (762) (((non-volatile or (non adj volatile)) adj

USPAT,US-PG-PUB,EPO,JPO,IBM,TDB

Default operator: OR

Highlight all hit terms in bold

(((non-volatile or (non adj volatile)) adj memory) and ((trapping
 adj layer) or (floating adj gate))) not (((("5070378" | "5200733" |
 "5852317" | "5966603" | "6151248" | "6222768" | "6337502").PN.)
 ("NROM" and (antenna adj effect)) ("NROM" and (antenna)) ("NROM" and
 (antenna)) not ("NROM" and (antenna adj effect)))) not
 (kuo-tung-cheng.in. liu-chien-hung.in. pan-shyi-shuh.in.
 huang-shou-wei.in.)) and (ground\$4)) and (antenna)) and ("ONO" or
 (oxide adj2 nitride adj3 oxide))

Search term Section Image Text HTML

	U	I	PT	P	Document ID	Issue Dat	Pages	Title	Current OR	Current XRef	R	Inventor	S	C
1	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 20030209740 A1	20031113	115	Semiconductor device	257/286	257/E23.055; 257/E23.069; 257/E25.023		Miyamoto, Toshio et al.	<input type="checkbox"/>	<input type="checkbox"/>
2	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 20030137007 A1	20030724	47	Flash memory device and fabrication process thereof, method of forming a dielectric	257/324			Ohmi, Tadaihiro et al.	<input type="checkbox"/>	<input type="checkbox"/>
3	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 20030128582 A1	20030710	45	Non-volatile memory and semiconductor device	365/185.03			Yamazaki, Shunpei et al.	<input type="checkbox"/>	<input type="checkbox"/>
4	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 20030075755 A1	20030424	33	NONVOLATILE MEMORY AND ELECTRONIC APPARATUS	257/315	257/E21.209; 257/E21.422; 257/E27.103;		YAMAZAKI, SHUNPEI	<input type="checkbox"/>	<input type="checkbox"/>
5	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 20020117742 A1	20020829	114	Semiconductor device	257/686	257/E23.055; 257/E23.069; 257/E25.023		Miyamoto, Toshio et al.	<input type="checkbox"/>	<input type="checkbox"/>
6	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 20020089051 A1	20020711	114	Semiconductor device	257/686	257/E23.055; 257/E23.069; 257/E25.023		Miyamoto, Toshio et al.	<input type="checkbox"/>	<input type="checkbox"/>
7	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 20020064070 A1	20020530	44	Non-volatile memory and semiconductor device	365/185.03			Yamazaki, Shunpei et al.	<input type="checkbox"/>	<input type="checkbox"/>
8	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 20020040847	20020411	44	Method of forming a dielectric film	204/192.22	257/E21.241; 257/E21.268;		Ohmi, Tadaihiro et al.	<input type="checkbox"/>	<input type="checkbox"/>